

ABSTRACT

Provided is a sputtering target with which it is possible to form a magnetic thin film having a high coercive force H_c and a process for production thereof.

5 The sputtering target is a sputtering target comprising metallic Co, metallic Pt, and an oxide, wherein the sputtering target does not contain metallic Cr, and the oxide has at least one of WO_3 and TiO_2 .